



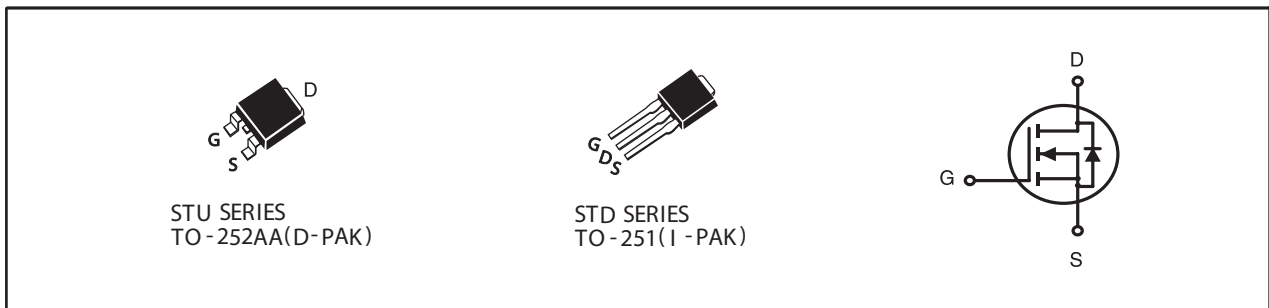
N-Channel Logic Level Enhancement Mode Field Effect Transistor

PRODUCT SUMMARY

V _{DSS}	I _D	R _{DS(ON)} (mΩ) Max
40V	38A	11 @ V _{GS} =10V
		15 @ V _{GS} =4.5V

FEATURES

- Super high dense cell design for low R_{DS(ON)}.
- Rugged and reliable.
- TO-252 and TO-251 Package.



ABSOLUTE MAXIMUM RATINGS (T_C=25°C unless otherwise noted)

Symbol	Parameter	Limit	Units
V _{DS}	Drain-Source Voltage	40	V
V _{GS}	Gate-Source Voltage	±20	V
I _D	Drain Current-Continuous	T _C =25°C	38
		T _C =70°C	30
I _{DM}	-Pulsed ^a	111	A
P _D	Maximum Power Dissipation	T _C =25°C	42
		T _C =70°C	27
T _J , T _{STG}	Operating Junction and Storage Temperature Range	-55 to 150	°C

THERMAL CHARACTERISTICS

R _{θJC}	Thermal Resistance, Junction-to-Case	3	°C/W
R _{θJA}	Thermal Resistance, Junction-to-Ambient	50	°C/W

STU/D466S

Ver 1.0

ELECTRICAL CHARACTERISTICS (T_C=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	40			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =32V , V _{GS} =0V			1	uA
I _{GSS}	Gate-Body Leakage Current	V _{GS} = ±20V , V _{DS} =0V			±100	nA
ON CHARACTERISTICS						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250uA	1	1.7	3	V
R _{DS(ON)}	Drain-Source On-State Resistance	V _{GS} =10V , I _D =19A		9.5	11	m ohm
		V _{GS} =4.5V , I _D =17A		11	15	m ohm
g _{FS}	Forward Transconductance	V _{DS} =5V , I _D =19A		55		S
DYNAMIC CHARACTERISTICS ^b						
C _{ISS}	Input Capacitance	V _{DS} =20V, V _{GS} =0V f=1.0MHz		2245		pF
C _{OSS}	Output Capacitance			321		pF
C _{RSS}	Reverse Transfer Capacitance			147		pF
SWITCHING CHARACTERISTICS ^b						
t _{D(ON)}	Turn-On Delay Time	V _{DD} =20V I _D =1A		35		ns
t _r	Rise Time			23		ns
t _{D(OFF)}	Turn-Off Delay Time	V _{GS} =10V R _{GEN} = 6 ohm		72		ns
t _f	Fall Time			42		ns
Q _g	Total Gate Charge	V _{DS} =20V, I _D =19A, V _{GS} =10V		29		nC
		V _{DS} =20V, I _D =19A, V _{GS} =4.5V		13		nC
Q _{gs}	Gate-Source Charge	V _{DS} =20V, I _D =19A, V _{GS} =10V		3.3		nC
Q _{gd}	Gate-Drain Charge			5.7		nC
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
V _{SD}	Diode Forward Voltage	V _{GS} =0V, I _S =7A		0.8	1.3	V
Notes						
a.Pulse Test:Pulse Width < 300us, Duty Cycle < 2%.						
b.Guaranteed by design, not subject to production testing.						

Feb,06,2013

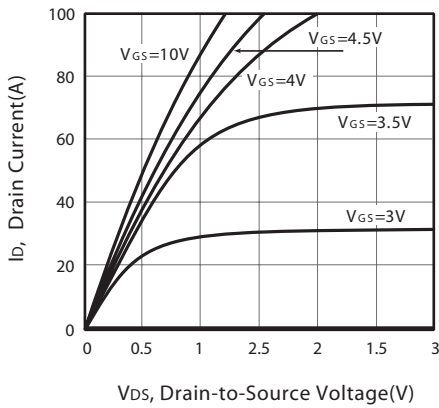


Figure 1. Output Characteristics

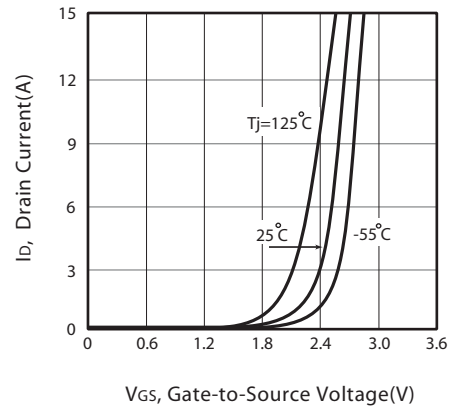


Figure 2. Transfer Characteristics

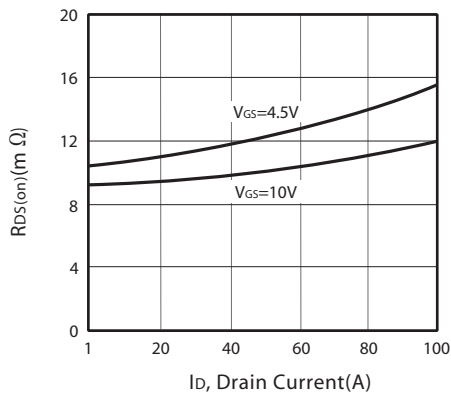


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

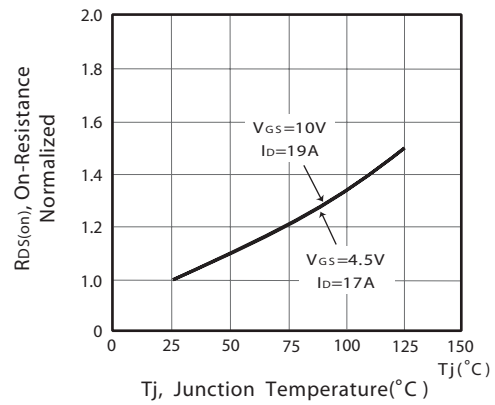


Figure 4. On-Resistance Variation with Drain Current and Temperature

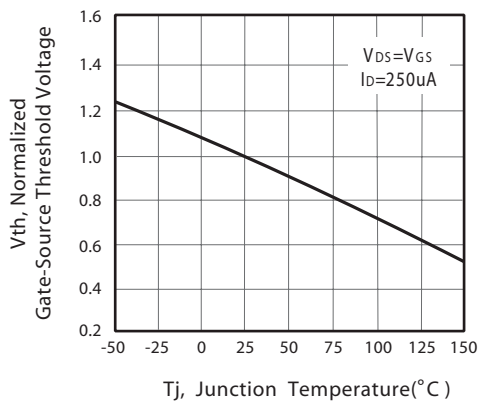


Figure 5. Gate Threshold Variation with Temperature

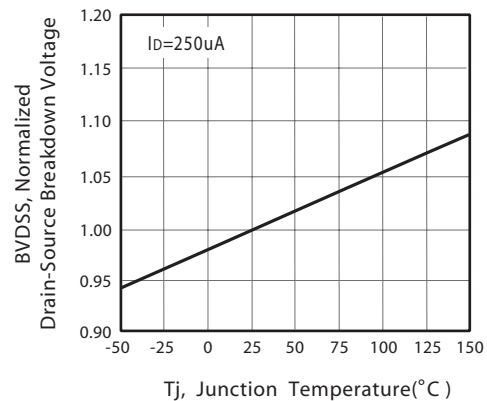


Figure 6. Breakdown Voltage Variation with Temperature

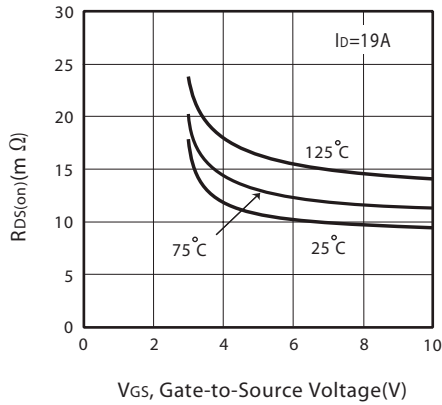


Figure 7. On-Resistance vs. Gate-Source Voltage

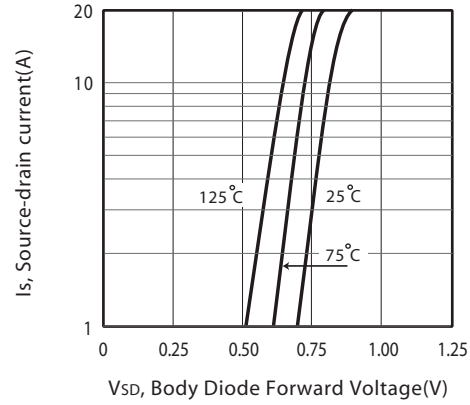


Figure 8. Body Diode Forward Voltage Variation with Source Current

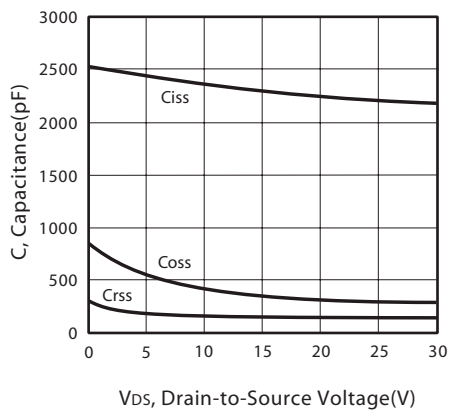


Figure 9. Capacitance

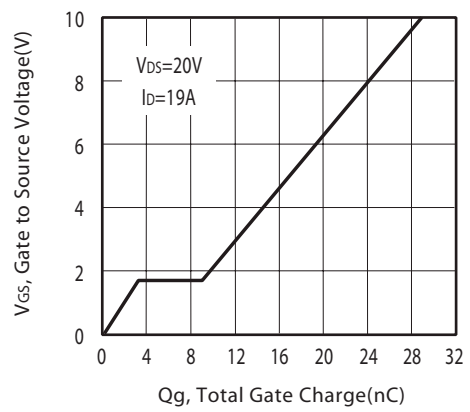


Figure 10. Gate Charge

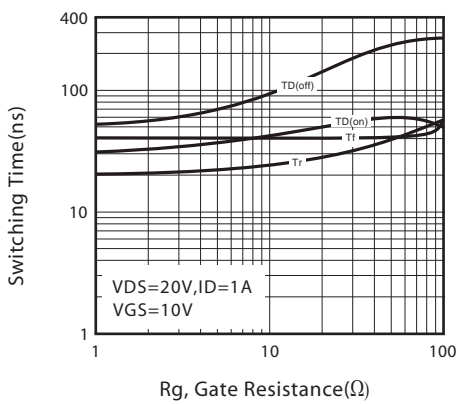


Figure 11. switching characteristics

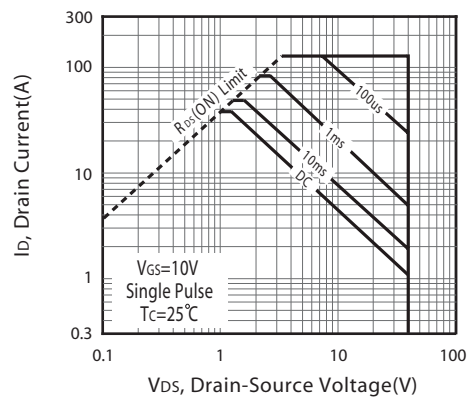


Figure 12. Maximum Safe Operating Area

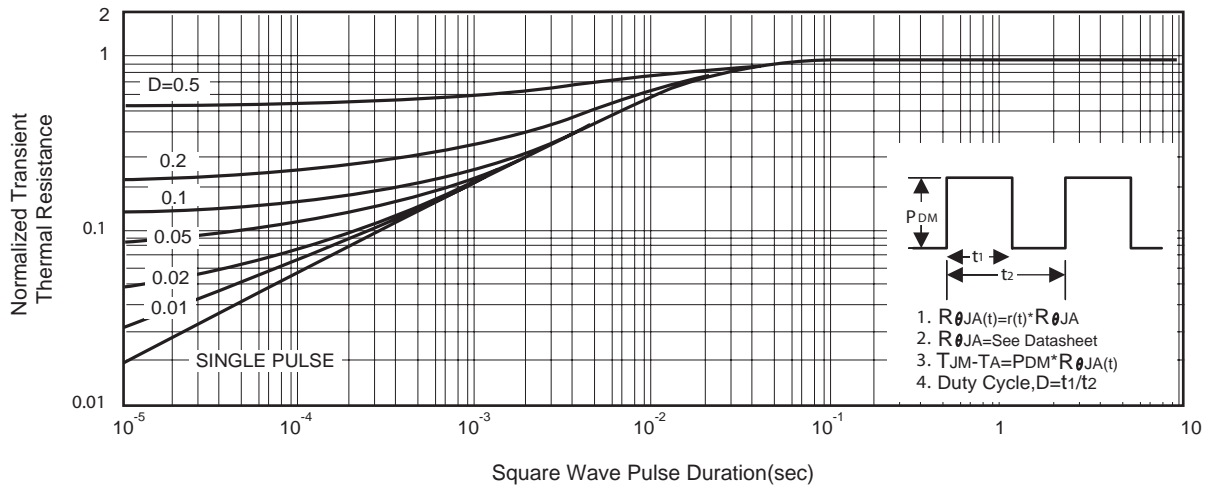
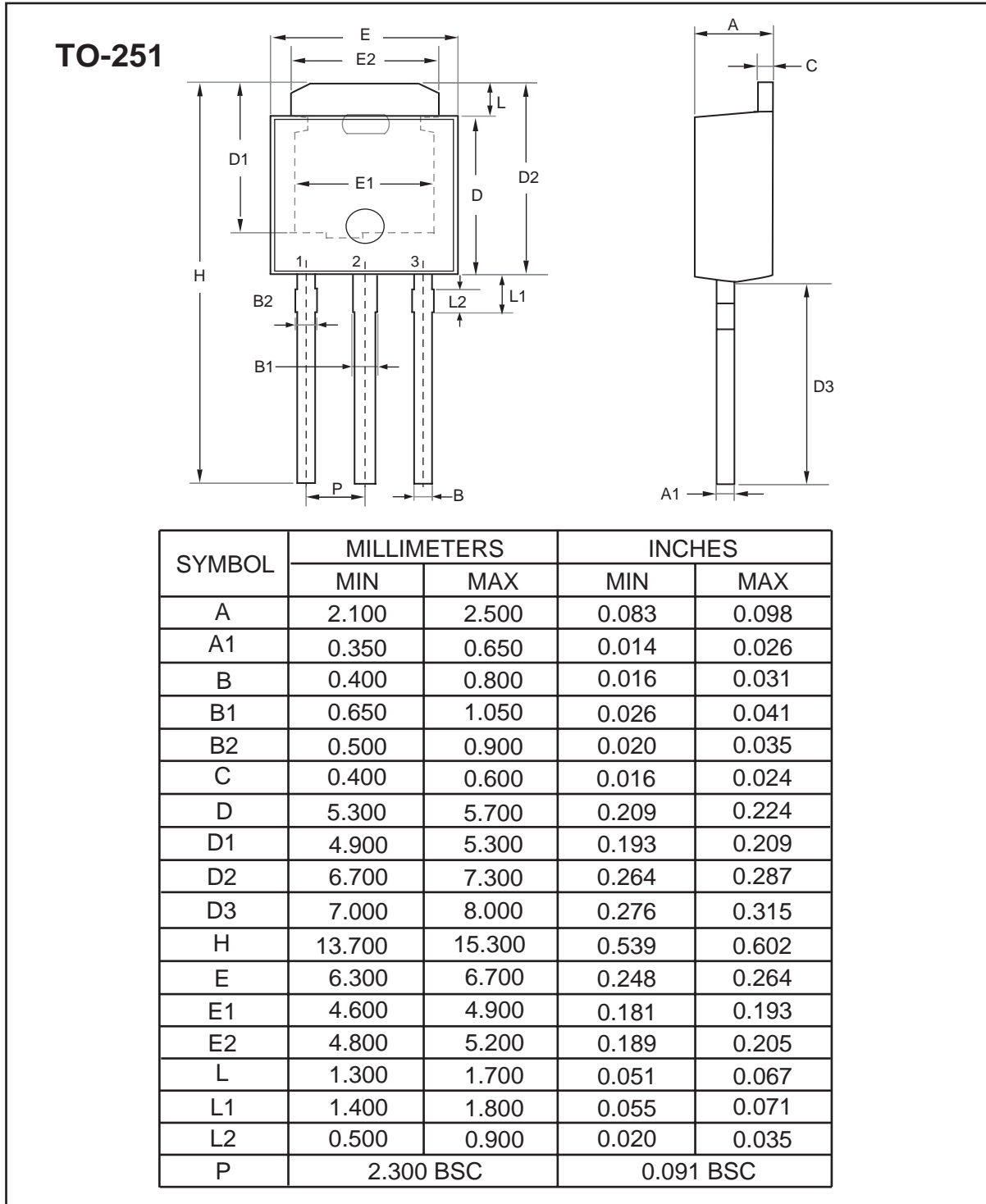
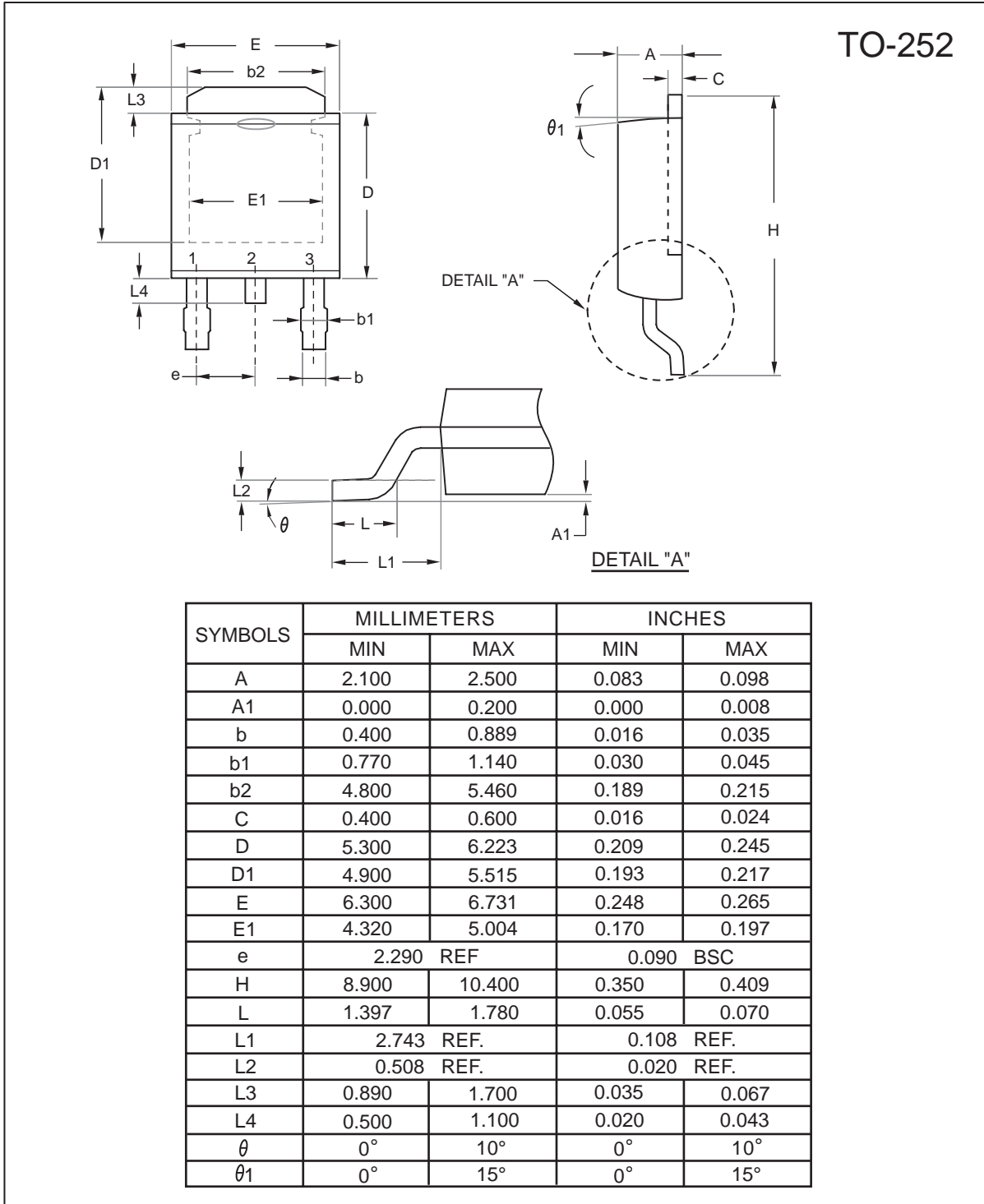


Figure 13. Normalized Thermal Transient Impedance Curve

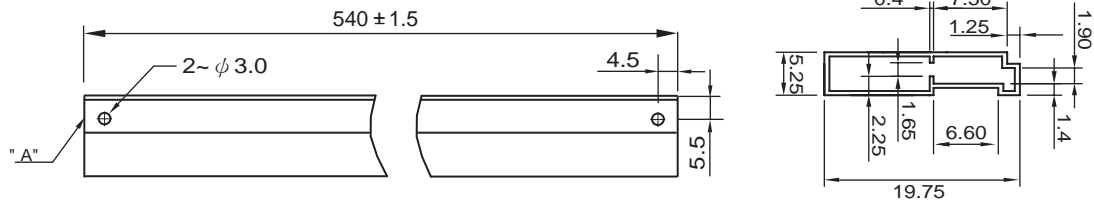
PACKAGE OUTLINE DIMENSIONS



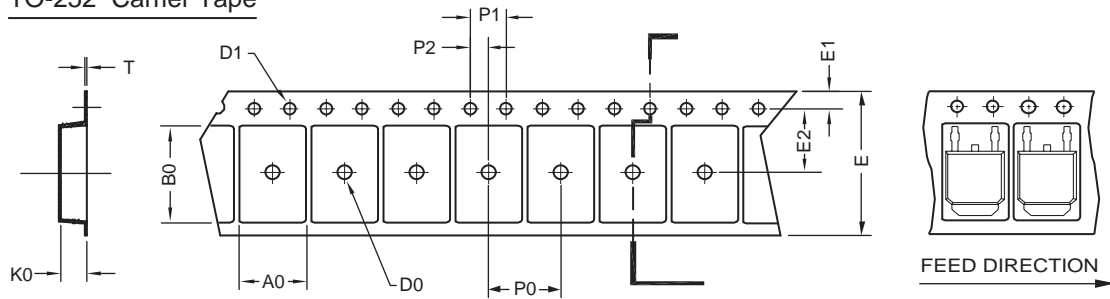


TO-251 Tube/TO-252 Tape and Reel Data

TO-251 Tube



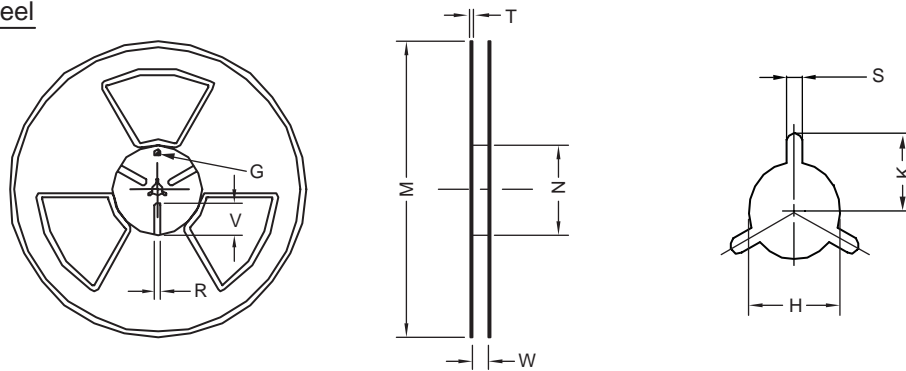
TO-252 Carrier Tape



UNIT:mm

PACKAGE	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T
TO-252 (16 mm)	6.96 ±0.1	10.49 ±0.1	2.79 ±0.1	φ 2	φ 1.5 +0.1 - 0	16.0 ±0.3	1.75 ±0.1	7.5 ±0.15	8.0 ±0.1	4.0 ±0.1	2.0 ±0.15	0.3 ±0.05

TO-252 Reel



UNIT:mm

TAPE SIZE	REEL SIZE	M	N	W	T	H	K	S	G	R	V
16 mm	φ 330	φ 330 ± 0.5	φ 97 ± 1.0	17.0 + 1.5 - 0	2.2	φ 13.0 + 0.5 - 0.2	10.6	2.0 ±0.5	---	---	---